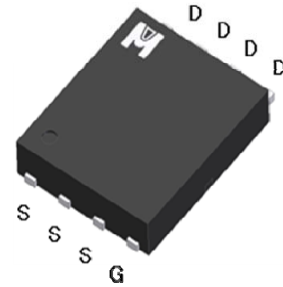


N-Channel Logic Level Enhancement Mode Field Effect Transistor

Product Summary:

BV_{DSS}	100V
$R_{DS(on)}$ (MAX.)	12m Ω
I_D	50A



UIS, Rg 100% Tested

Pb-Free Lead Plating & Halogen Free



ABSOLUTE MAXIMUM RATINGS ($T_A = 25\text{ }^\circ\text{C}$ Unless Otherwise Noted)

PARAMETERS/TEST CONDITIONS		SYMBOL	LIMITS	UNIT
Gate-Source Voltage		V_{GS}	± 20	V
Continuous Drain Current	$T_C = 25\text{ }^\circ\text{C}$	I_D	50	A
	$T_C = 100\text{ }^\circ\text{C}$		31	
Pulsed Drain Current ¹		I_{DM}	110	
Avalanche Current		I_{AS}	20	
Avalanche Energy	$L = 0.1\text{mH}, I_D = 21\text{A}, R_G = 25\Omega$	E_{AS}	22	mJ
Repetitive Avalanche Energy ²	$L = 0.05\text{mH}$	E_{AR}	11	
Power Dissipation	$T_C = 25\text{ }^\circ\text{C}$	P_D	50	W
	$T_C = 100\text{ }^\circ\text{C}$		20	
Operating Junction & Storage Temperature Range		T_{j}, T_{stg}	-55 to 150	$^\circ\text{C}$

THERMAL RESISTANCE RATINGS

THERMAL RESISTANCE	SYMBOL	TYPICAL	MAXIMUM	UNIT
Junction-to-Case	$R_{\theta JC}$		2.5	$^\circ\text{C}/\text{W}$
Junction-to-Ambient	$R_{\theta JA}$		50	

¹Pulse width limited by maximum junction temperature.

²Duty cycle $\leq 1\%$

ELECTRICAL CHARACTERISTICS (T_J = 25 °C, Unless Otherwise Noted)

PARAMETER	SYMBOL	TEST CONDITIONS	LIMITS			UNIT
			MIN	TYP	MAX	
STATIC						
Drain-Source Breakdown Voltage	V _{(BR)DSS}	V _{GS} = 0V, I _D = 250μA	100			V
Gate Threshold Voltage	V _{GS(th)}	V _{DS} = V _{GS} , I _D = 250μA	1.0	2.0	3.0	
Gate-Body Leakage	I _{GSS}	V _{DS} = 0V, V _{GS} = ±12V			±100	nA
Zero Gate Voltage Drain Current	I _{DSS}	V _{DS} = 80V, V _{GS} = 0V			1	μA
		V _{DS} = 70V, V _{GS} = 0V, T _J = 125 °C			25	
On-State Drain Current ¹	I _{D(ON)}	V _{DS} = 5V, V _{GS} = 10V	50			A
Drain-Source On-State Resistance ¹	R _{DS(ON)}	V _{GS} = 10V, I _D = 12A		10	12	mΩ
		V _{GS} = 4.5V, I _D = 10A		12	15	
Forward Transconductance ¹	g _{fs}	V _{DS} = 5V, I _D = 12A		45		S
DYNAMIC						
Input Capacitance	C _{iss}	V _{GS} = 0V, V _{DS} = 50V, f = 1MHz		2130		pF
Output Capacitance	C _{oss}			336		
Reverse Transfer Capacitance	C _{rss}			29		
Gate Resistance	R _g	V _{GS} = 15mV, V _{DS} = 0V, f = 1MHz		1.5		Ω
Total Gate Charge ^{1,2}	Q _g (V _{GS} =10V)	V _{DS} = 50V, V _{GS} = 10V, I _D = 12A		38		nC
	Q _g (V _{GS} =4.5V)			23		
Gate-Source Charge ^{1,2}	Q _{gs}			10		
Gate-Drain Charge ^{1,2}	Q _{gd}			8.2		
Turn-On Delay Time ^{1,2}	t _{d(on)}	V _{DS} = 50V, I _D = 12A, V _{GS} = 10V, R _{GS} = 6Ω		6		nS
Rise Time ^{1,2}	t _r			10		
Turn-Off Delay Time ^{1,2}	t _{d(off)}			8		
Fall Time ^{1,2}	t _f			25		
SOURCE-DRAIN DIODE RATINGS AND CHARACTERISTICS (T_C = 25 °C)						
Continuous Current	I _S				50	A
Pulsed Current ³	I _{SM}				110	
Forward Voltage ¹	V _{SD}	I _F = 12A, V _{GS} = 0V			1.2	V
Reverse Recovery Time	t _{rr}	I _F = 12A, dI _F /dt = 100A / μS		30		nS
Reverse Recovery Charge	Q _{rr}				130	

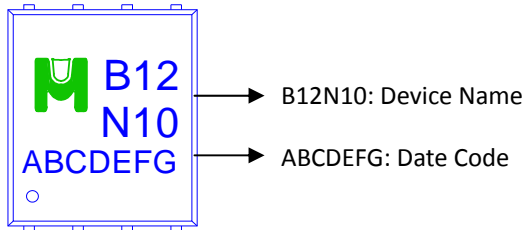
¹Pulse test : Pulse Width ≤ 300 μsec, Duty Cycle ≤ 2%.

²Independent of operating temperature.

³Pulse width limited by maximum junction temperature.

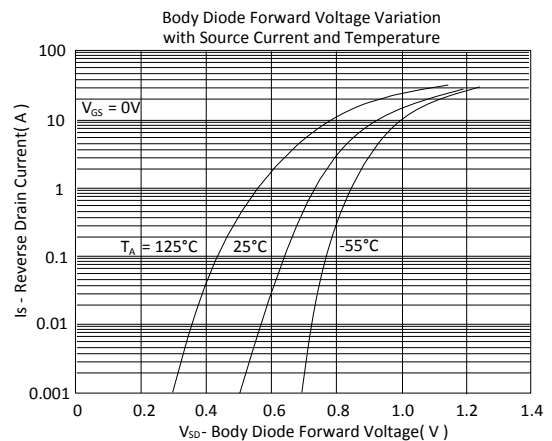
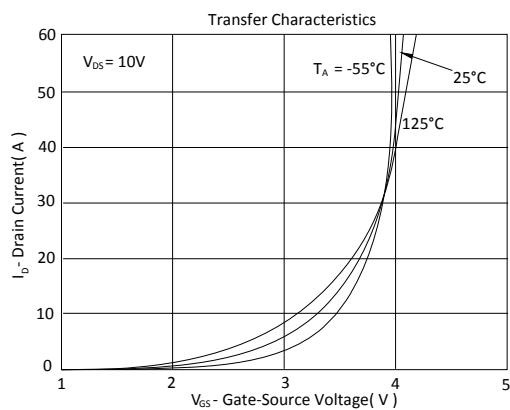
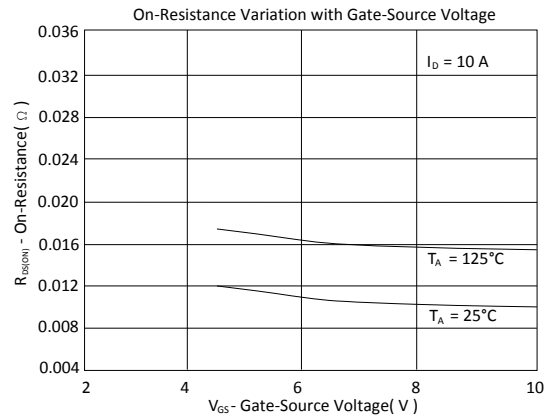
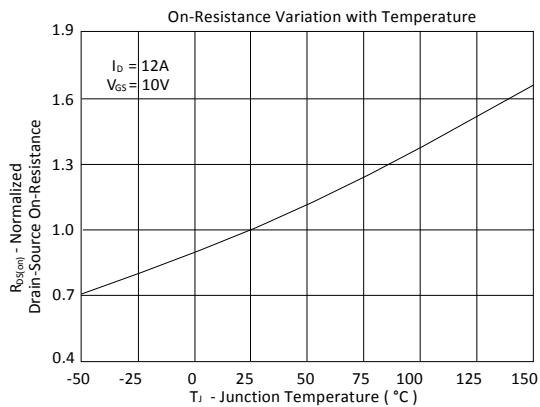
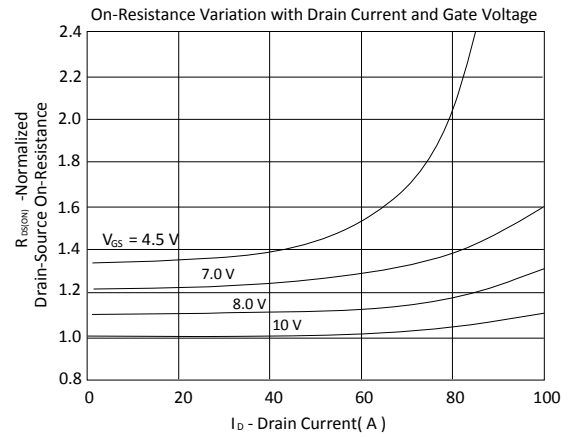
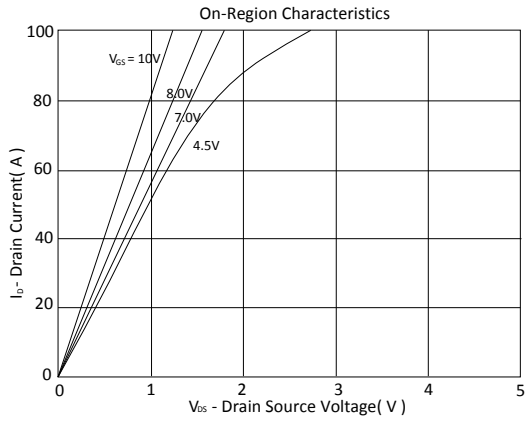
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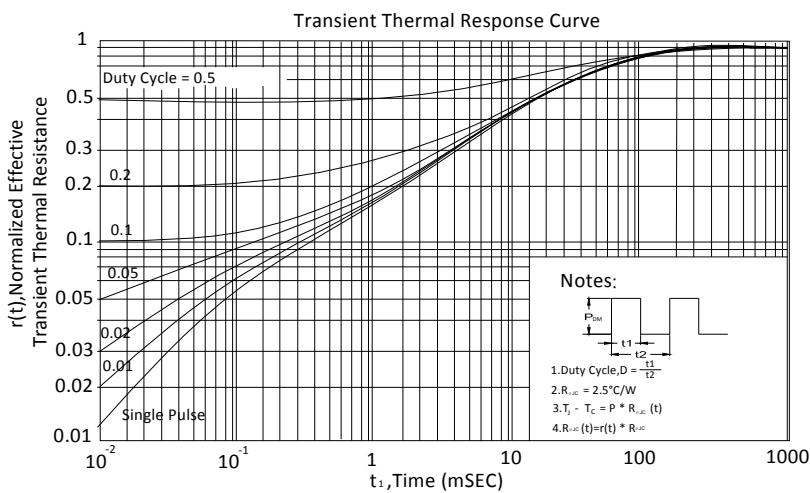
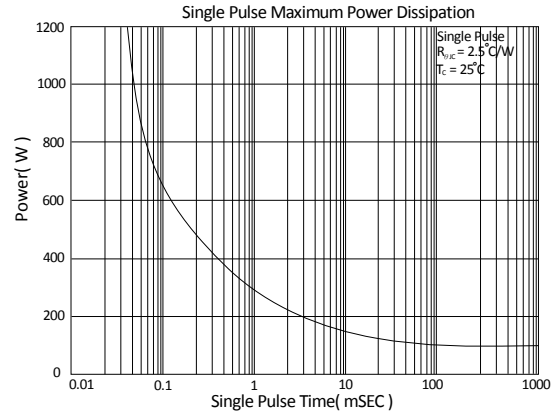
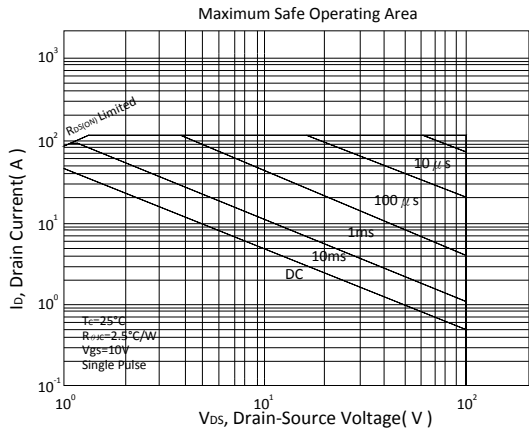
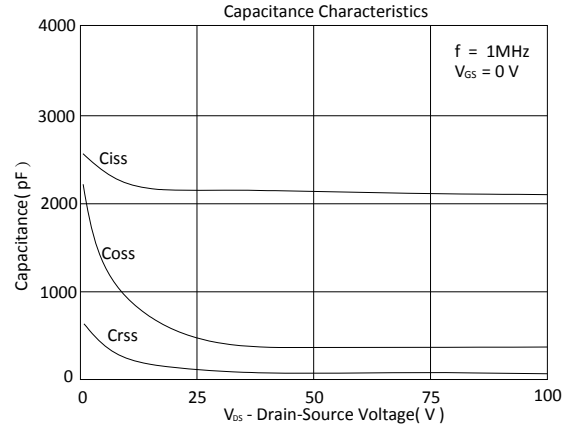
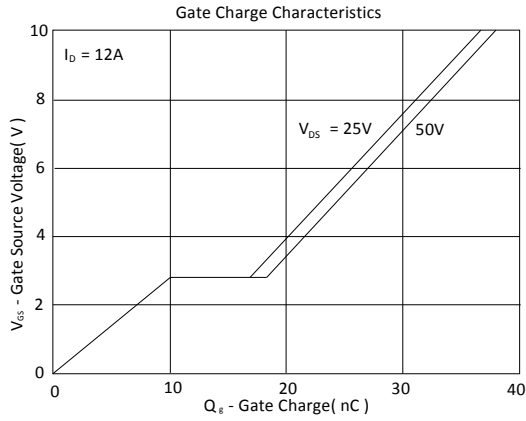
Device Name: EMB12N10H for EDFN 5 x 6





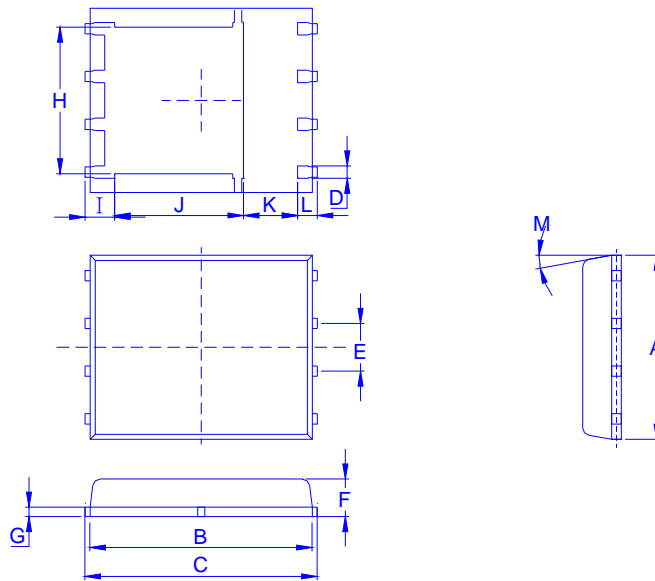
TYPICAL CHARACTERISTICS







Outline Drawing



Dimension in mm

Dimension	A	B	C	D	E	F	G	H	I	J	K	L	M
Min.	4.80	5.50	5.90	0.3		0.85	0.15	3.67	0.41	3.00	0.94	0.45	0°
Typ.					1.27								
Max.	5.30	5.90	6.15	0.51		1.20	0.30	4.54	0.85	3.92	1.7	0.71	12°

Recommended minimum pads

